

1N5391 – 1N5399

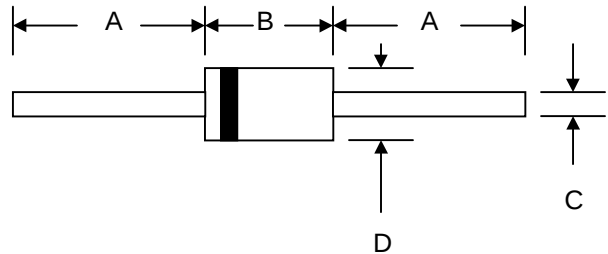
1.5A SILICON RECTIFIER

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-15		
Dim	Min	Max
A	25.4	—
B	5.50	7.62
C	0.71	0.864
D	2.60	3.60
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.



Characteristic	Symbol	1N 5391	1N 5392	1N 5393	1N 5395	1N 5397	1N 5398	1N 5399	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 75°C	I _O	1.5							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	50							A
Forward Voltage @I _F = 1.5A	V _{FM}	1.0							V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5.0 50							μA
Typical Junction Capacitance (Note 2)	C _j	30							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}	50							K/W
Operating Temperature Range	T _j	-65 to +125							°C
Storage Temperature Range	T _{STG}	-65 to +150							°C

***Glass passivated forms are available upon request**

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.